

uA741

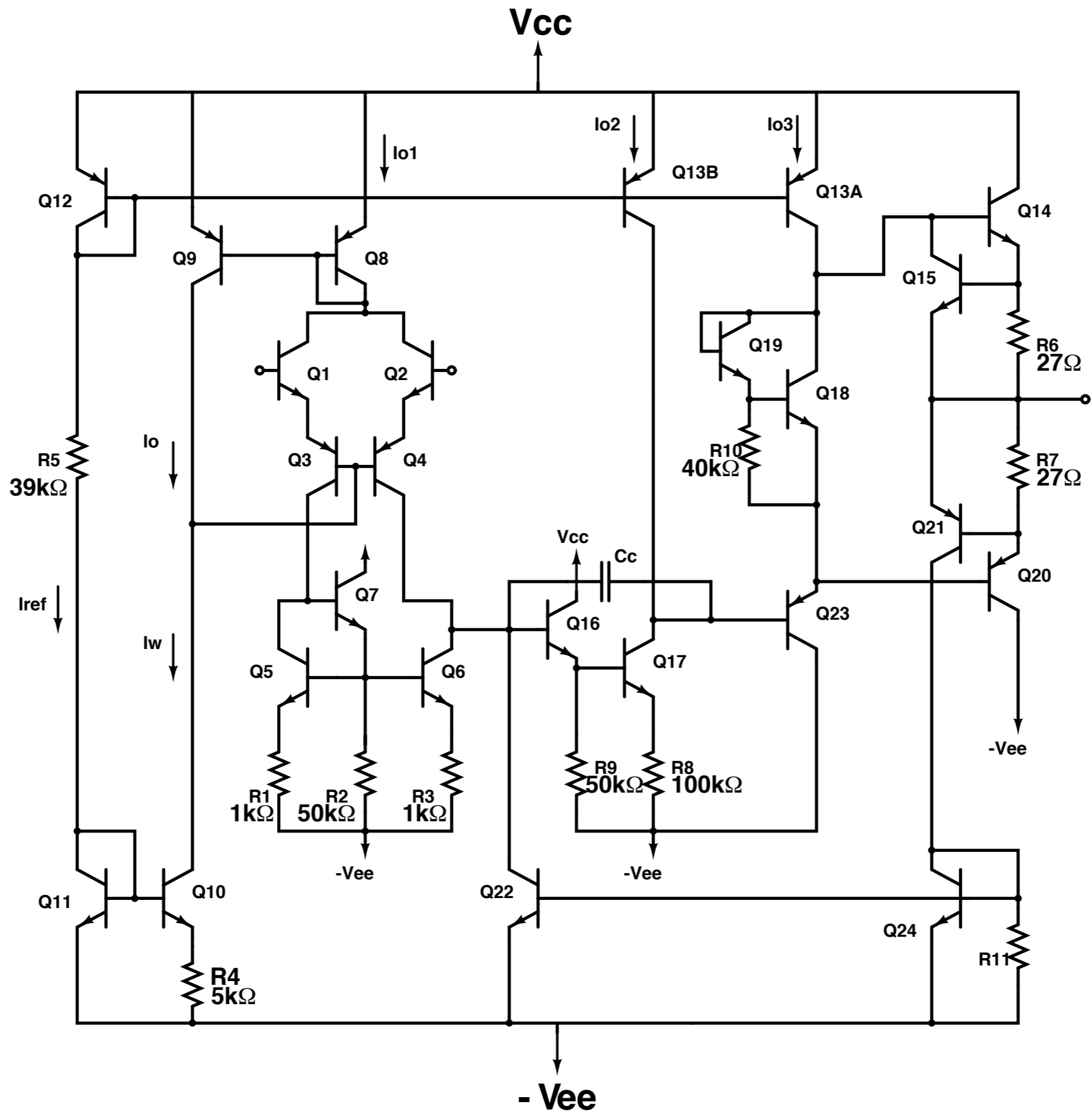
INEL4202 - Fall 2009

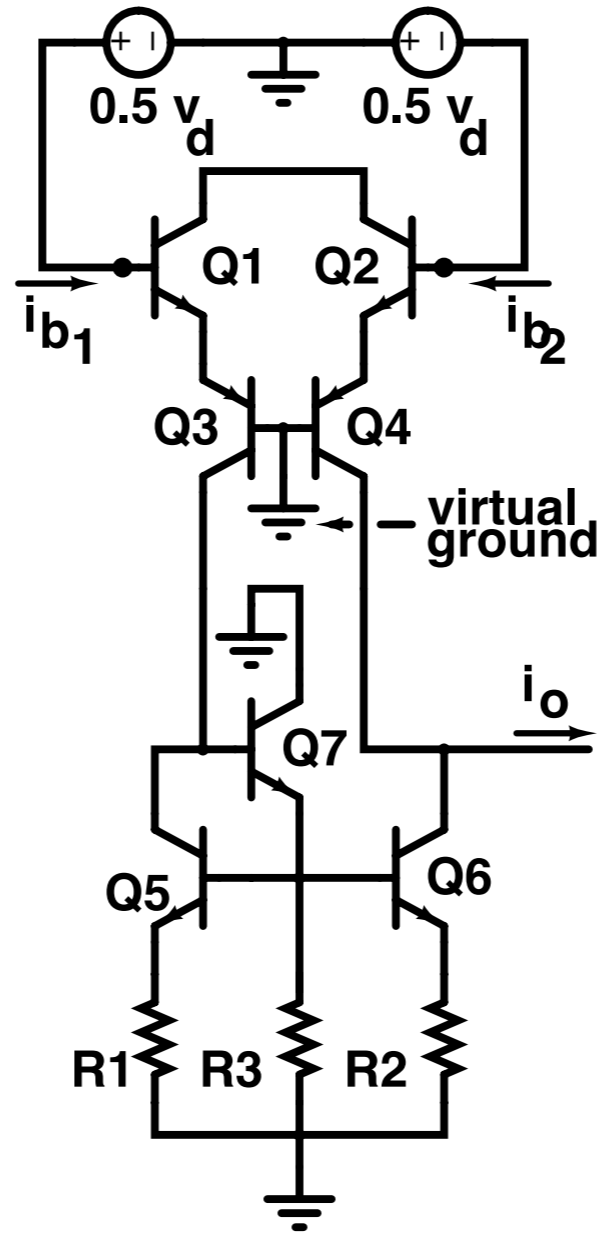
Device Parameters

Parameter	npn	pnp
I_S	10^{-14} A	10^{-14} A
β	200	50
V_A	125	50

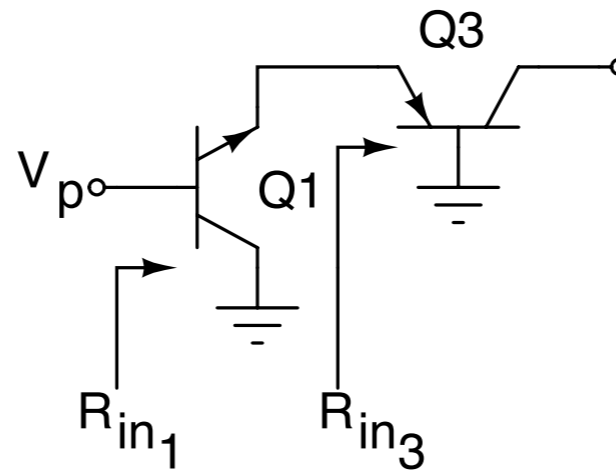
For Q_{13A} and Q_{13B} assume I_S equal to 0.25×10^{-14} A and 0.75×10^{-14} A, respectively.

The area of power transistors Q_{14} and Q_{20} is assumed to be three times that of regular transistors.





- INPUT RESISTANCE

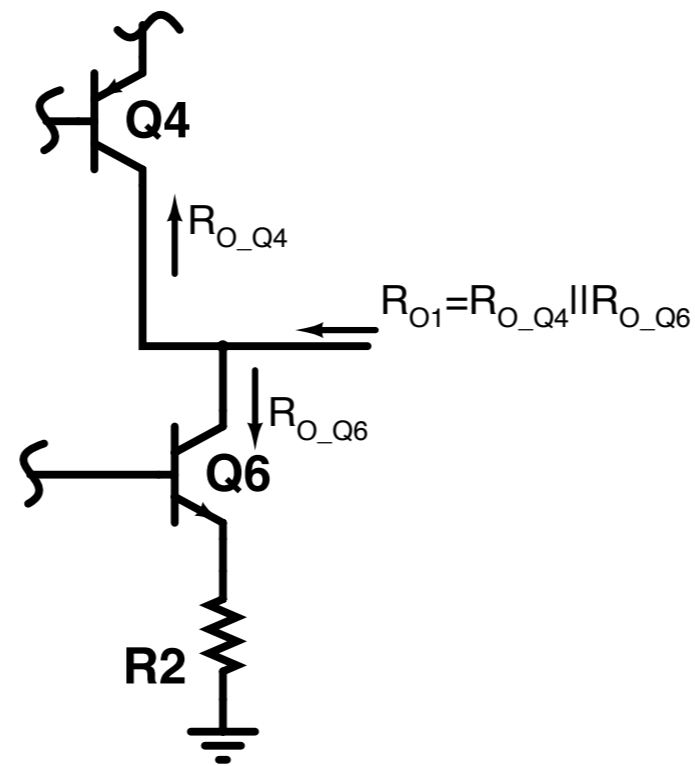


$$R_{in1} = r_{\pi1} + (\beta_N + 1)R_{in3} = r_{\pi1} + (\beta_N + 1)\frac{V_T}{I_{e2}} \approx 2r_{\pi1}$$

For differential signals: $R_{in} = 4r_{\pi1}$.

- OUTPUT RESISTANCE

$$R_{O1} = R_{O-Q4} \parallel R_{O-Q6}$$



For Q6:

$$R_{O-Q6} = r_{O6}(1 + g_{m6}R_2)$$

For Q4:

$$R_{O-Q4} = r_{O4}(1 + g_{m4}R_{eQ4})$$

where R_{eQ4} is the small signal equivalent resistance at the emitter of Q4. Thus

$$R_{eQ4} = r_{e2}$$

and

$$R_{O-Q4} = r_{O4}(1 + g_{m4}r_{e2})$$

Using $I_{C4} = I_{C6} = 9.5\mu A$, we get the following values:

Quantity	Value
$g_{m4} = g_{m6}$	$\frac{I_{C4}}{V_T} = \frac{9.5\mu A}{25mV} = 0.38mA/V$
r_{e2}	$\frac{V_T}{I_{e2}} \approx \frac{25mV}{9.5\mu A} = 2.63k\Omega$
r_{O4}	$\frac{V_{A_{npn}}}{I_{C4}} = \frac{50V}{9.5\mu A} = 5.26M\Omega$
r_{O6}	$\frac{V_{A_{npn}}}{I_{C6}} = \frac{125V}{9.5\mu A} = 13.16M\Omega$
R_{O-Q4}	$5.26M\Omega \left(1 + 0.38\frac{mA}{V} \times 2.63k\Omega\right) = 10.5M\Omega$
R_{O-Q6}	$13.16M\Omega \left(1 + 0.38\frac{mA}{V} \times 1k\Omega\right) = 18.16M\Omega$
R_{O1}	$10.5M\Omega \parallel 18.16M\Omega = 6.65M\Omega$

- TRANSCONDUCTANCE

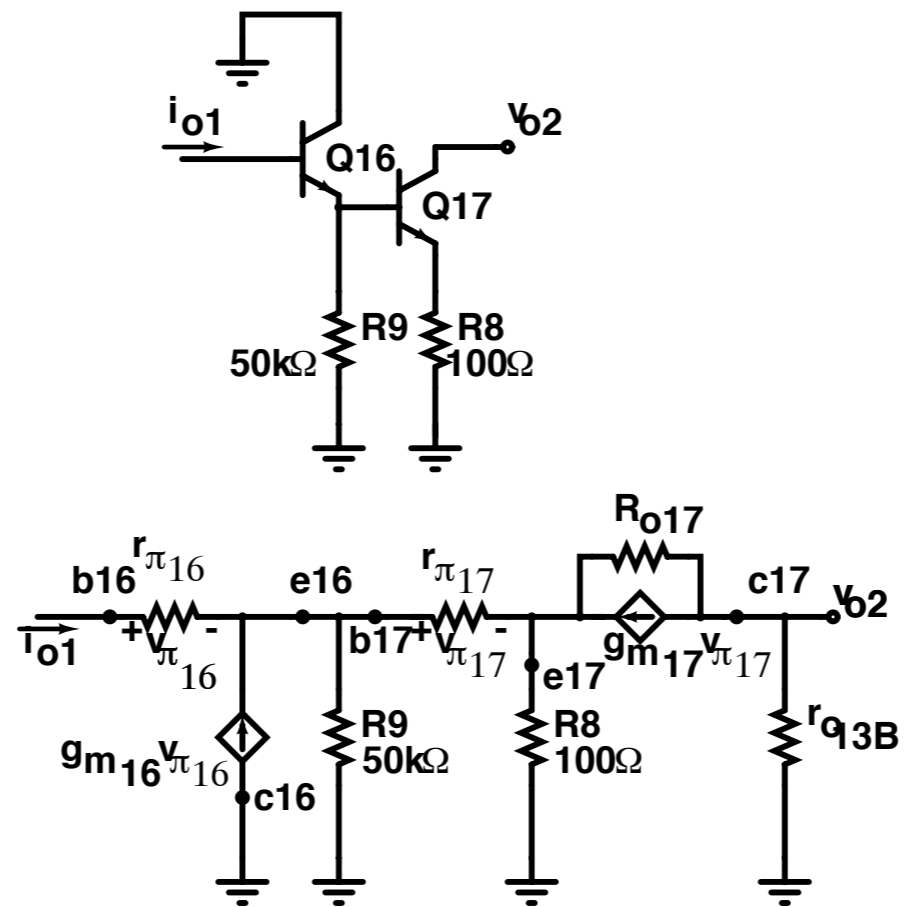
$$G_{M1} = \frac{i_{O1}}{v_d}$$

Use $i_{O1} = -i_{C6} - i_{C4} = -2i_{e1}$ and $i_{e1} = (\beta + 1)\frac{v_d/2}{2r_\pi} = v_d \times \frac{1}{4r_{e1}}$.

Thus

$$G_{M1} = -\frac{1}{2r_{e1}} = -\frac{1}{2}g_{m1} = -\frac{19.5\mu A}{225mV} = -0.19\frac{mA}{V}$$

Second Stage



- INPUT RESISTANCE

$$R_{in2} = r_{\pi16} + (\beta_{npn} + 1) \times (R9 \parallel (r_{\pi17} + (\beta_{npn} + 1)R8))$$

Using $I_{C16} = 16.2\mu A$ and $I_{C17} = 550\mu A$, we get $r_{\pi16} = 200 \frac{25mV}{16.2\mu A} = 308.6k\Omega$ and $r_{\pi17} = 200 \frac{25mV}{550\mu A} = 9.09k\Omega$. Thus we get

$$R_{in2} = 308.6k\Omega + 201 (50k\Omega \parallel (9.09k\Omega + 201 \times 100\Omega)) = 4M\Omega$$

- TRANSRESISTANCE

$$R_{M2} = \frac{v_{O2}}{i_{O1}} = \frac{v_{O2}}{v_{b16}/R_{in2}} = R_{in2} \times \frac{v_{O2}}{v_{b16}}$$

The output voltage at the collector of Q_{17} depends on the collector resistance. Let this resistance be R_{c17} . Then

$$R_{c17} = r_{o17}(1 + g_{m17}R_8) \parallel r_{o13B}$$

From $I_{C17} = I_{C13B} = 550\mu A$, $r_{o17} = \frac{V_{Anpn}}{I_{C17}} = \frac{125V}{550\mu A} = 227k\Omega$
and $r_{o13B} = \frac{50V}{550\mu A} = 90.9k\Omega$. Thus

$$R_{c17} = 90.9k\Omega \parallel 227k\Omega \times \left(1 + \frac{550\mu A}{25mV} 100\Omega\right) = 80.8k\Omega$$

Using this value, we get

$$\begin{aligned}R_{M2} &= R_{in2} \times \frac{R_{e16}}{r_{e16} + R_{e16}} \times \frac{-g_{m17}R_{c17}}{1 + g_{m17}R_8} \\ &= 4M\Omega \times \frac{18.43k\Omega}{18.43k\Omega + \frac{25mV}{16.2\mu A}} \times \frac{-\frac{550\mu A}{25mV}80.8k\Omega}{1 + \frac{550\mu A}{25mV}100\Omega} \\ &= 4M\Omega \times 0.92 \times -556 = -2044M\Omega\end{aligned}$$

Notice that this can be expressed as a transconductance

$$G_{M2} = \frac{i_{O2}}{v_{i1}} = \frac{-v_{O2} \div R_{c17}}{i_{i1} \times R_{i2}} = \frac{R_{M2}}{R_{i2} \times R_{c17}} = \frac{-2044M\Omega}{4M\Omega \times 80.8k\Omega} = 6.3 \frac{mA}{V}$$

Compare this result with the textbook's of $G_{M2} = 6.5mA/V$ (see page 829).

- OUTPUT RESISTANCE

$$R_{o2} = R_{c17} = 76.9k\Omega$$

Voltage Gain of Stages One and Two

The gain $A_v = \frac{v_{o2}}{v_d}$ can be found from:

$$\frac{v_{o2}}{v_d} = \frac{i_{o1}}{v_d} \times \frac{R_{o1}}{R_{o1} + R_{i2}} \times \frac{v_{o2}}{i_{i2}}$$

Noticing that $i_{o1} = i_{i2}$ and using our previous results,

$$A_v = \frac{v_{o2}}{v_d} = -0.19 \frac{mA}{V} \times \frac{6.65M\Omega}{6.65M\Omega + 4M\Omega} \times -2044M\Omega = 2.42 \times 10^5$$